

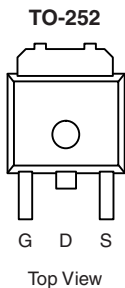
P-Channel 30-V (D-S), MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a
- 30	0.010 at $V_{GS} = - 10$ V	- 15
	0.018 at $V_{GS} = - 4.5$ V	- 12

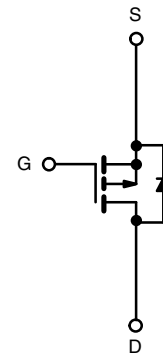
FEATURES

- TrenchFET[®] Power MOSFETs


RoHS
COMPLIANT


Drain Connected to Tab

Ordering Information: SUD45P03-10-E3 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	- 30	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ^b	I_D	$T_A = 25$ °C	- 15	A
		$T_A = 100$ °C	- 8	
Pulsed Drain Current	I_{DM}	- 100		
Continuous Source Current (Diode Conduction)	I_S	- 15		
Maximum Power Dissipation ^b	P_D	$T_C = 25$ °C	70	W
		$T_A = 25$ °C	4 ^b	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}		30	°C/W
Maximum Junction-to-Case	R_{thJC}		1.8	

Notes:

a. Calculated Rating for $T_A = 25$ °C, for comparison purposes only. This cannot be used as continuous rating (see Absolute Maximum Ratings and Typical Characteristics).

b. Surface Mounted on FR4 board, $t \leq 10$ s.

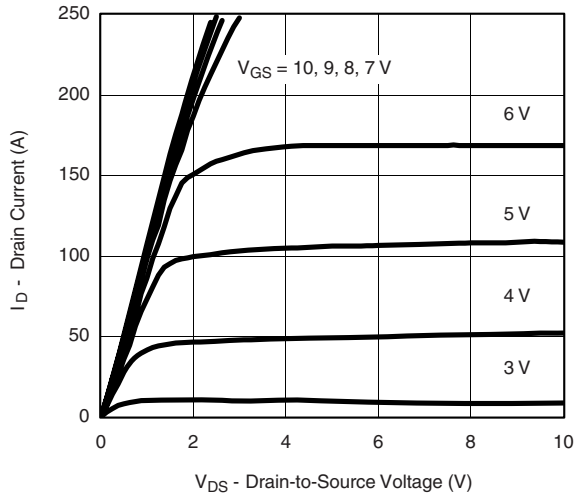
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1.0		- 3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			- 50	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	- 50			A
		$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	- 20			
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -15\text{ A}$			0.010	Ω
		$V_{GS} = -10\text{ V}, I_D = -15\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.015	
		$V_{GS} = -4.5\text{ V}, I_D = -15\text{ A}$			0.018	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -15\text{ A}$	20			S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$		6000		μF
Output Capacitance	C_{oss}			1100		
Reverse Transfer Capacitance	C_{rss}			700		
Total Gate Charge ^c	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -45\text{ A}$		90	150	nC
Gate-Source Charge ^c	Q_{gs}			20		
Gate-Drain Charge ^c	Q_{gd}			16		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 0.33\text{ }\Omega$ $I_D \cong -45\text{ A}, V_{GEN} = -10\text{ V}, R_G = 2.4\text{ }\Omega$		15	25	ns
Rise Time ^c	t_r			375	550	
Turn-Off Delay Time ^c	$t_{d(off)}$			100	200	
Fall Time ^c	t_f			140	250	
Source-Drain Diode Ratings and Characteristic $T_C = 25\text{ }^\circ\text{C}$						
Pulsed Current	I_{SM}				100	A
Diode Forward Voltage ^a	V_{SD}	$I_F = -45\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -45\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		55	100	ns

Notes:

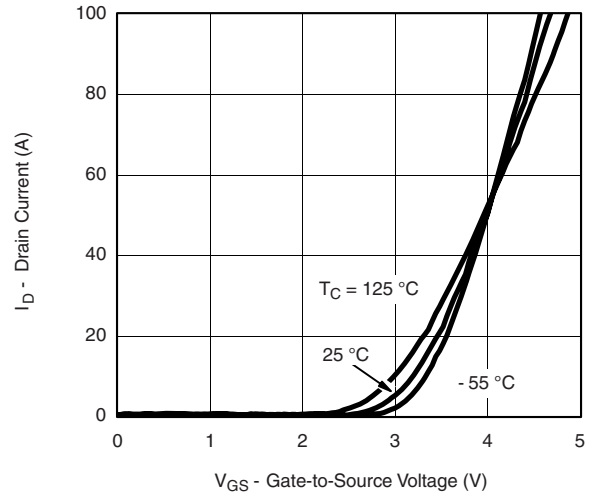
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

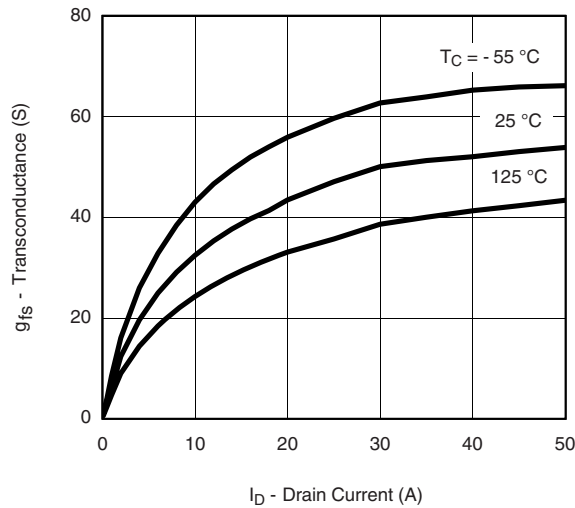
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



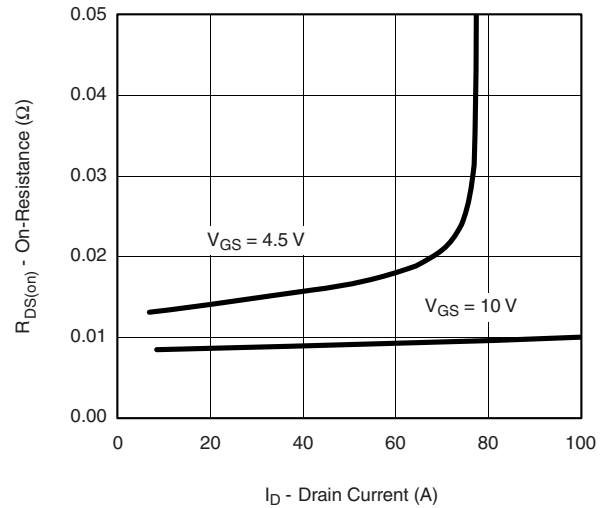
Output Characteristics



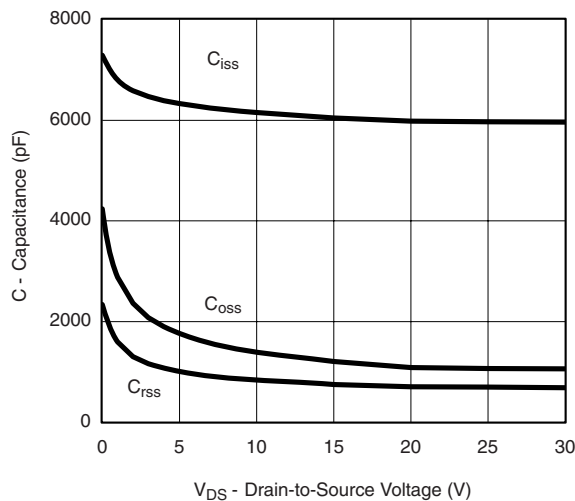
Transfer Characteristics



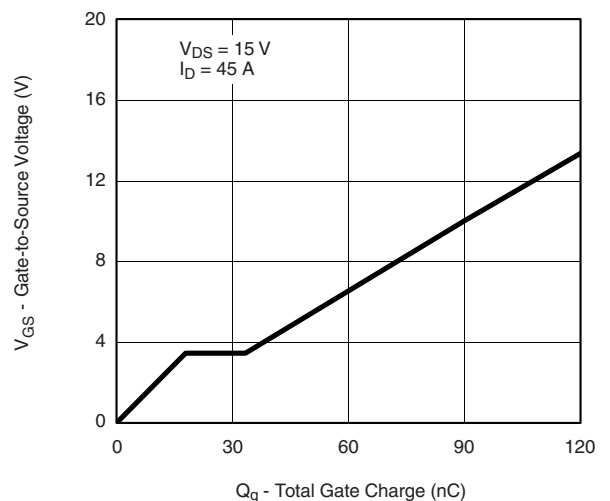
Transconductance



On-Resistance vs. Drain Current

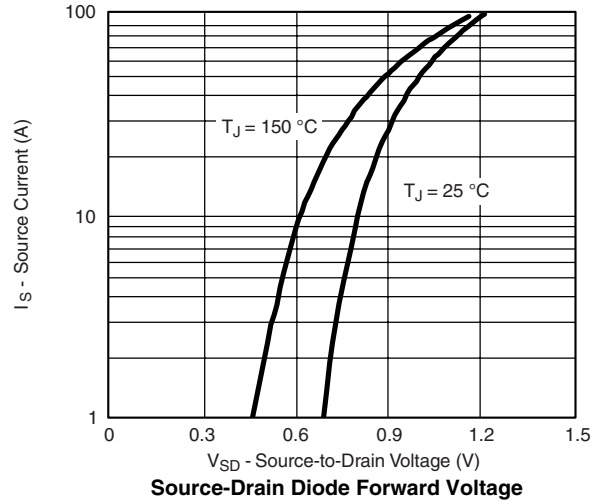
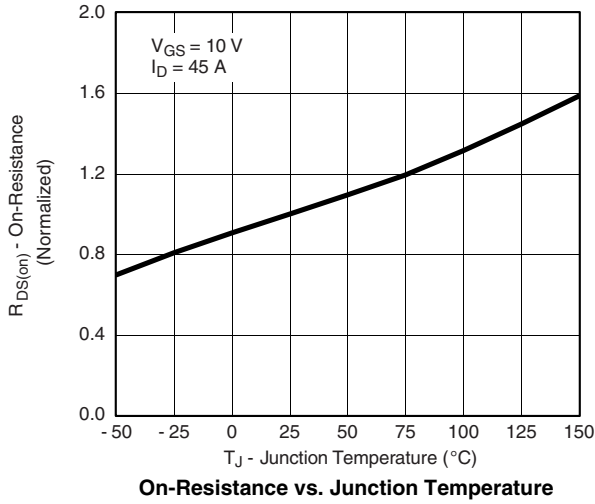


Capacitance

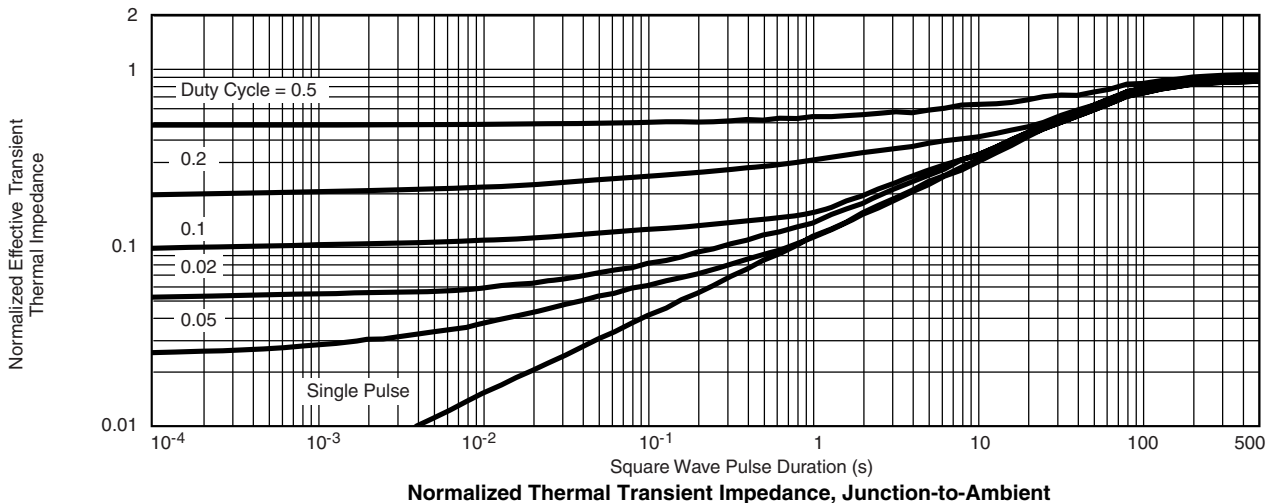
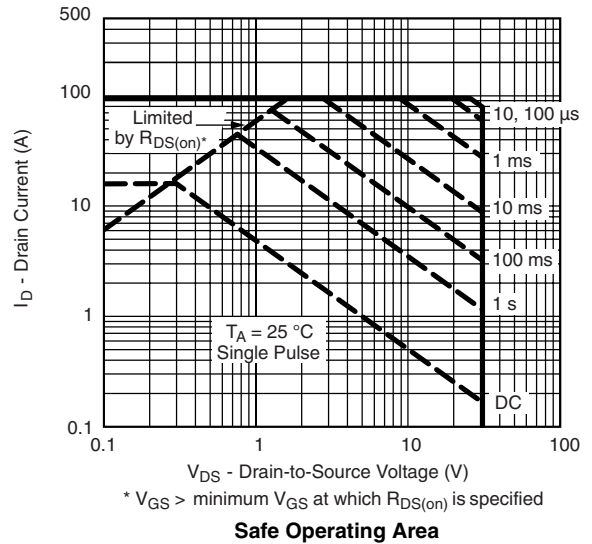
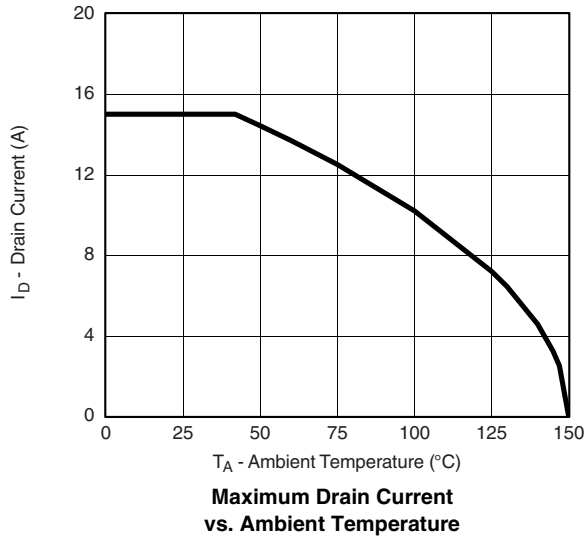


Gate Charge

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



THERMAL RATINGS



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?70766>.



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.